•	Application No.	Applicant(s)	
Notice of Allowshills	10/721,978	JUNG ET AL.	
Notice of Allowability	Examiner	Art Unit	
	Alonzo Chambliss	2814	
The MAILING DATE of this communication apperation apperation allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIFE of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this app or other appropriate communication GHTS. This application is subject to	olication. If not include will be mailed in due	ed course. THIS
1. This communication is responsive to <u>10/28/04</u> .		·	
2. The allowed claim(s) is/are 1-17.			
3. \boxtimes The drawings filed on <u>25 November 2003</u> are accepted by	the Examiner.		
 4. Acknowledgment is made of a claim for foreign priority un a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have 1. Certified copies not received: * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give 1. CORRECTED DRAWINGS (as "replacement sheets") must (a) including changes required by the Notice of Draftsperson 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1.5 each sheet. Replacement sheet(s) should be labeled as such in the 1. Correction of the depose 1. Correction of the dep	been received. been received in Application No cuments have been received in this in of this communication to file a reply ENT of this application. tted. Note the attached EXAMINER' as reason(s) why the oath or declarate t be submitted. on's Patent Drawing Review (PTO- as Amendment / Comment or in the October of the Amendment of the drawing the header according to 37 CFR 1.121(consist of BIOLOGICAL MATERIAL In	national stage applical complying with the red S AMENDMENT or Nation is deficient. 948) attached office action of the ligs in the front (not the light).	quirements
attached Examiner's comment regarding REQUIREMENT F Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☑ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No./Mail Date	5. ☐ Notice of Informal P 6. ☐ Interview Summary Paper No./Mail Dat	HE DEPOSIT OF BIOLOGICAL MATERIAL. 5. □ Notice of Informal Patent Application (PTO-152) 6. □ Interview Summary (PTO-413), Paper No./Mail Date 7. ☑ Examiner's Amendment/Comment	O-152)
4. Examiner's Comment Regarding Requirement for Deposit of Biological Material Output Description:	8. ⊠ Examiner's Stateme 9. □ Other	nt of Reasons for Allo	wance

DETAILED ACTION

Election/Restrictions

1. Applicant's election without traverse of claims 1-17 in the reply filed on 10/28/04 is acknowledged. Claim 18 has been cancelled.

Priority

2. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

EXAMINER'S AMENDMENT

3. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

SPECIFICATION:

The title has been changed to "METHOD OF FORMING A CONTACT IN A SEMICONDUCTOR DEVICE UTILIZING A PLASMA TREATMENT".

Allowable Subject Matter

4. The following is a statement of reasons for the indication of allowance subject matter: the prior art of record does not teach or suggest the combination of an insulating layer on a substrate, wherein the insulating layer is etched to form a contact hole. A

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silicon layer that is deposited on the sidewalls and an undersurface of the contact hole, wherein a silicon spacer is formed on the sidewalls of the contact hole by etching the silicon layer. Plasma treating silicon to form a silicon nitride spacer. Depositing a diffusion barrier on the silicon nitride spacer and filling the contact hole with tungsten in claims 1 and 11.

The prior art made of record and not relied upon is cited primarily to show the product of the instant invention.

Any inquiry concerning the communication or earlier communications from the examiner should be directed to Alonzo Chambliss whose telephone number is (571) 272-1927.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the group receptionist whose telephone number is (703) 308-7956.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system Status information for published applications may be obtained from either Private PMR or Public PMR. Status information for unpublished applications is available through Private PMR only. For more information about the PMR system see http://pair-dkect.uspto.gov. Should you have questions on access to the Private PMR system contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free) or EBC Support@uspto.gov.

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Primary Patent Examiner Art Unit 2814

AC/December 20, 2004